

### General Description

The QM3016M3/N3 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The QM3016M3/N3 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

### Product Summary

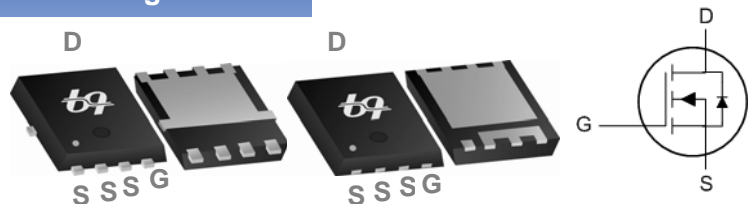


BVDSS	RDSON	ID
30V	4mΩ	80A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

### Pin Configuration



QM3016M3

QM3016N3

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	62	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	16	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	160	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	317	mJ
$I_{AS}$	Avalanche Current	53.8	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	43.4	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	75	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	2.88	$^\circ C/W$

### Electrical Characteristics ( $T_J=25\text{ }^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25\text{ }^\circ\text{C}$ , $I_D=1mA$	---	0.0213	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=30A$	---	3.4	4	m $\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	5.2	6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.73	---	mV/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25\text{ }^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=24V, V_{GS}=0V, T_J=55\text{ }^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=5V, I_D=30A$	---	26.5	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.4	2.8	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=20V, V_{GS}=4.5V, I_D=12A$	---	31.6	---	nC
$Q_{gs}$	Gate-Source Charge		---	6.07	---	
$Q_{gd}$	Gate-Drain Charge		---	13.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=1.5\Omega$ $I_D=20A$	---	11.2	---	ns
$T_r$	Rise Time		---	49	---	
$T_{d(off)}$	Turn-Off Delay Time		---	35	---	
$T_f$	Fall Time		---	7.8	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	3075	---	pF
$C_{oss}$	Output Capacitance		---	400	---	
$C_{rss}$	Reverse Transfer Capacitance		---	315	---	

### Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	$V_{DD}=25V, L=0.1mH, I_{AS}=30A$	98	---	---	mJ

### Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	80	A
$I_{SM}$	Pulsed Source Current <sup>2,6</sup>		---	---	160	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25\text{ }^\circ\text{C}$	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=53.8A$
- 4.The power dissipation is limited by  $175\text{ }^\circ\text{C}$  junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications , should be limited by total power dissipation.

### Typical Characteristics

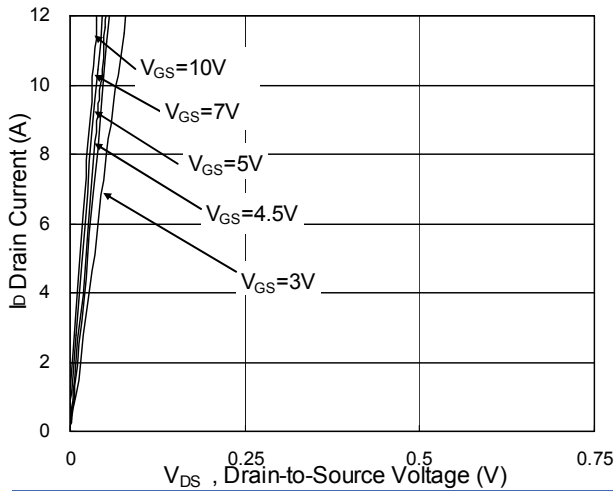


Fig.1 Typical Output Characteristics

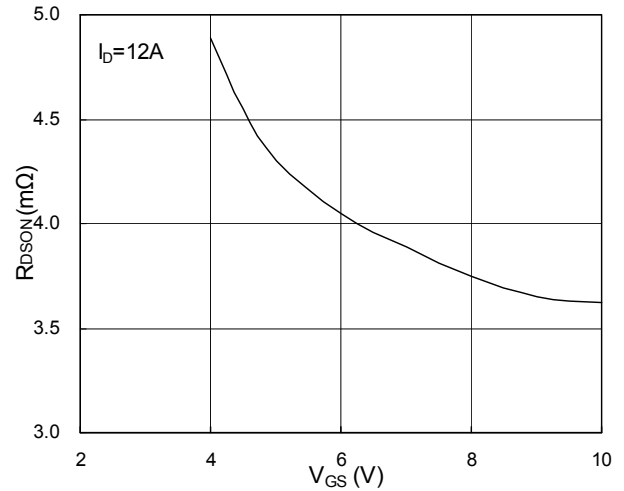


Fig.2 On-Resistance vs. G-S Voltage

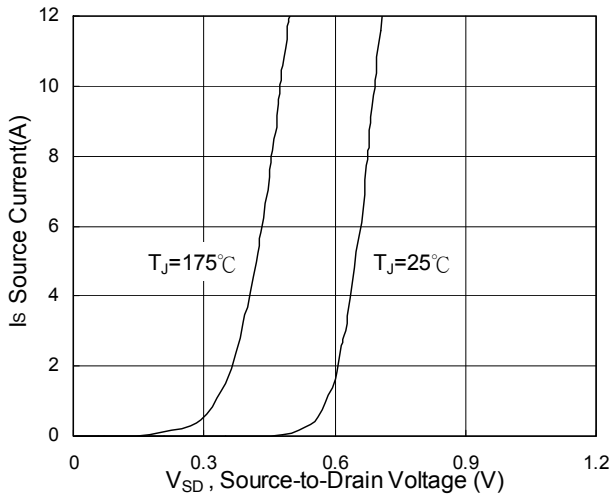


Fig.3 Forward Characteristics of Reverse

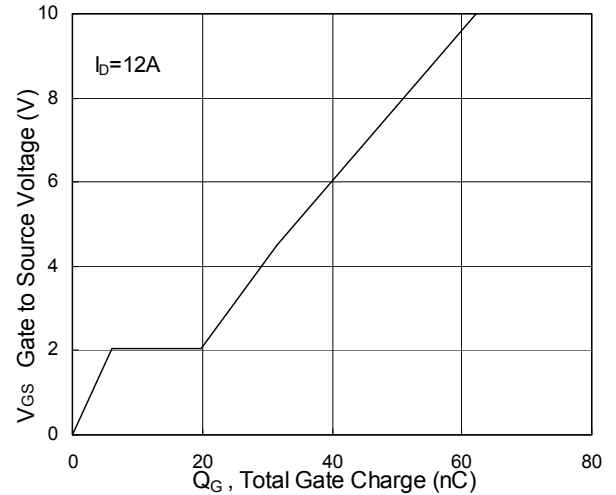


Fig.4 Gate-Charge Characteristics

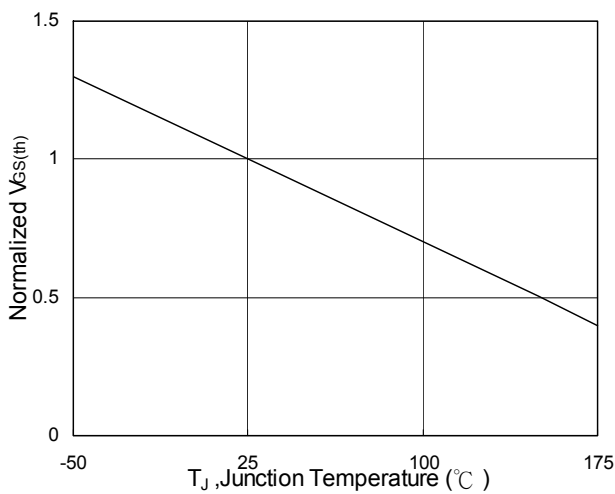


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

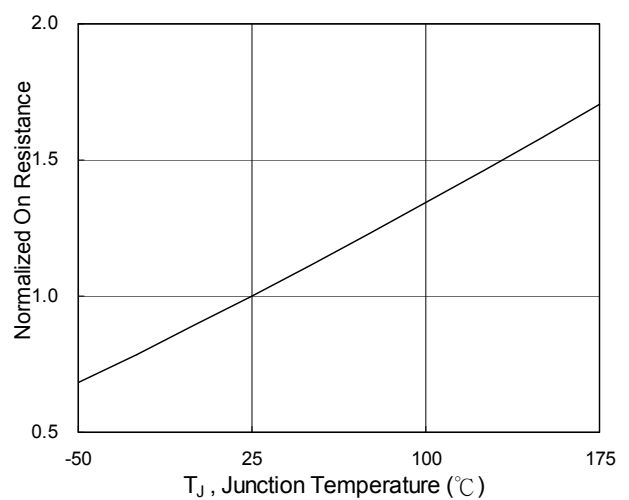


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

## N-Ch 30V Fast Switching MOSFETs

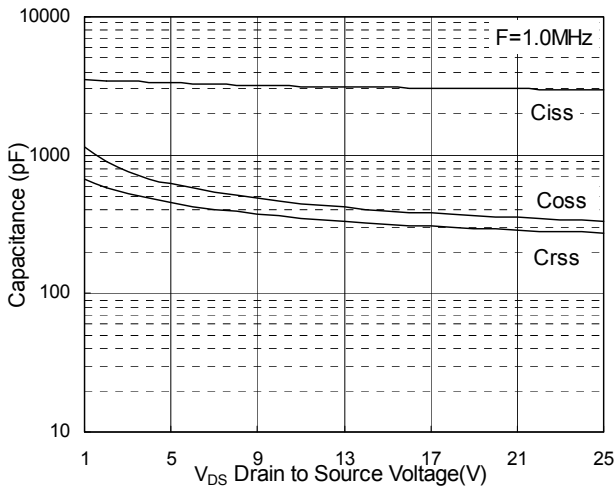


Fig.7 Capacitance

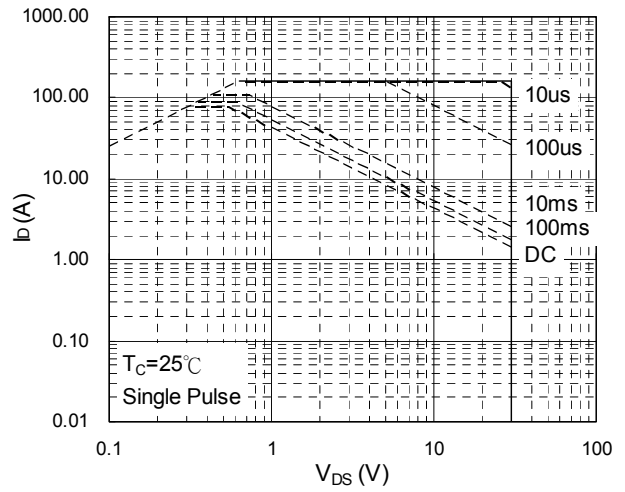


Fig.8 Safe Operating Area

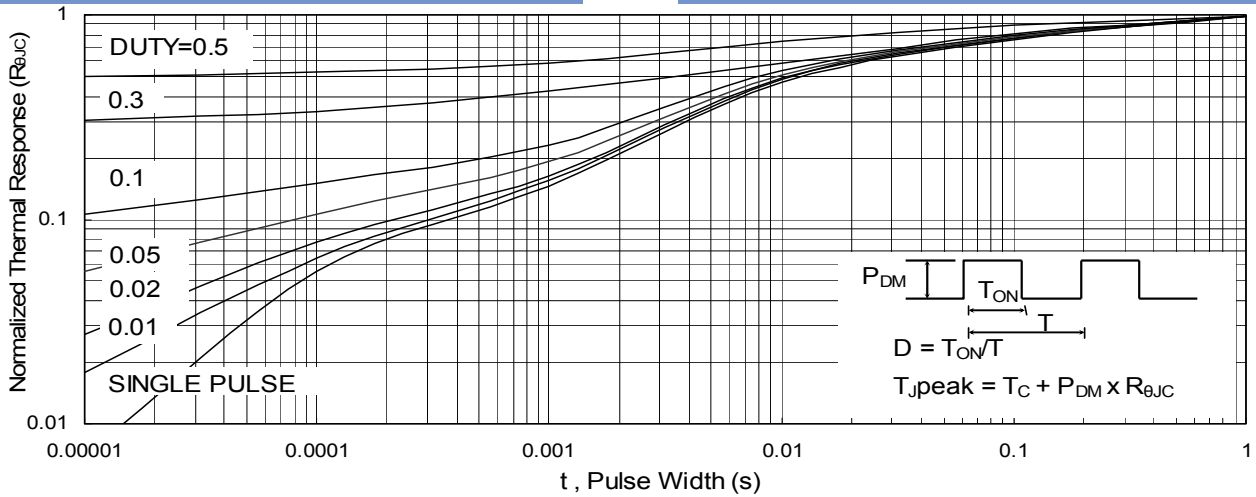


Fig.9 Normalized Maximum Transient Thermal Impedance

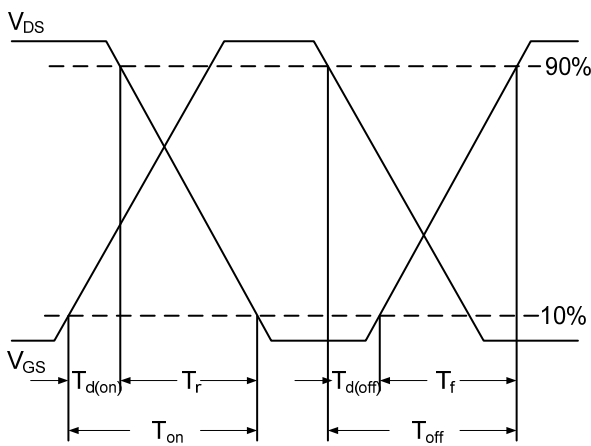


Fig.10 Switching Time Waveform

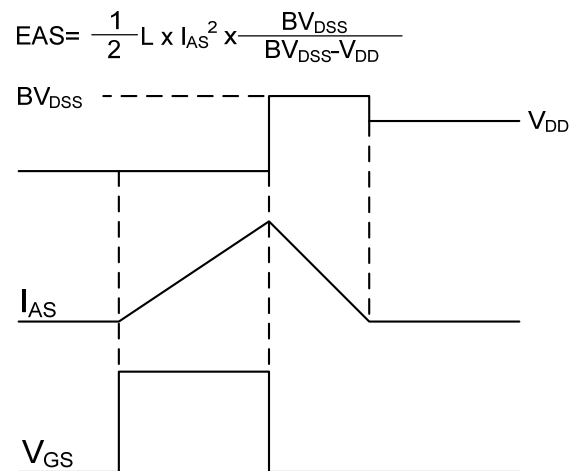


Fig.11 Unclamped Inductive Waveform